

Secondary Side Synchronous Rectifier (SR)

FEATURES

- Secondary Side Synchronous Rectifier(SR) for Flyback converters
- Supports High-Side and Low-Side in DCM and Quasi-Resonant Topologies
- <300uA Low Quiescent Current
- Built-in HV Supplies without Aux-Winding for VDD supply
- Integrated with 45V Power MOSFET
- Built-in Protections:
 - VDD UVLO
 - VDD Clamper by >5mA sink current
- Available with SOP-7 Package

APPLICATIONS

- Flyback converters
- Chargers

TYPICAL APPLICATION CIRCUIT

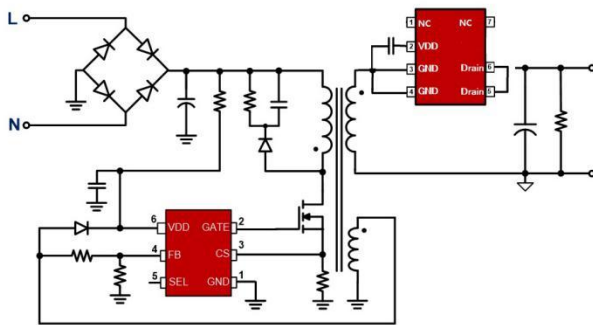
GENERAL DESCRIPTION

DP3510 is a family of secondary side synchronous rectifier, that replaced Schottky diodes by combined with an ultra low on-state resistance power MOSFET for high-efficiency flyback converters. It supports High-Side and Low-Side in DCM and Quasi-Resonant Topologies.

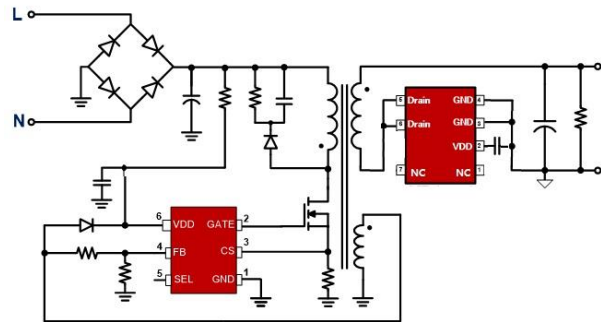
DP3510 is built-in HV supplies for VDD capacitor, that can eliminate the aux-winding of VDD supply for cost saving.

DP3510 integrates protections of Under Voltage Lockout (UVLO), VDD Clamper.

High Side SR



Low Side SR

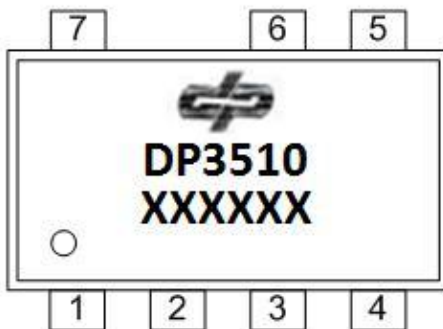


Pin Configuration



SOP-7

Marking Information



NOTE:

DP3510 for product name;

DP3510 is Product name; XXXXXX The first X represents the last year, 2014 is 4; The second X represents the month, in A-L 12 letters; The third and fourth X on behalf of the date, 01-31 said; The last two X represents the wafer batch code.

Output Power Table

Part Number	Package	BV for Internal MOSFET	System Operation Mode
DP3510	SOP-7	45V	QR or DCM

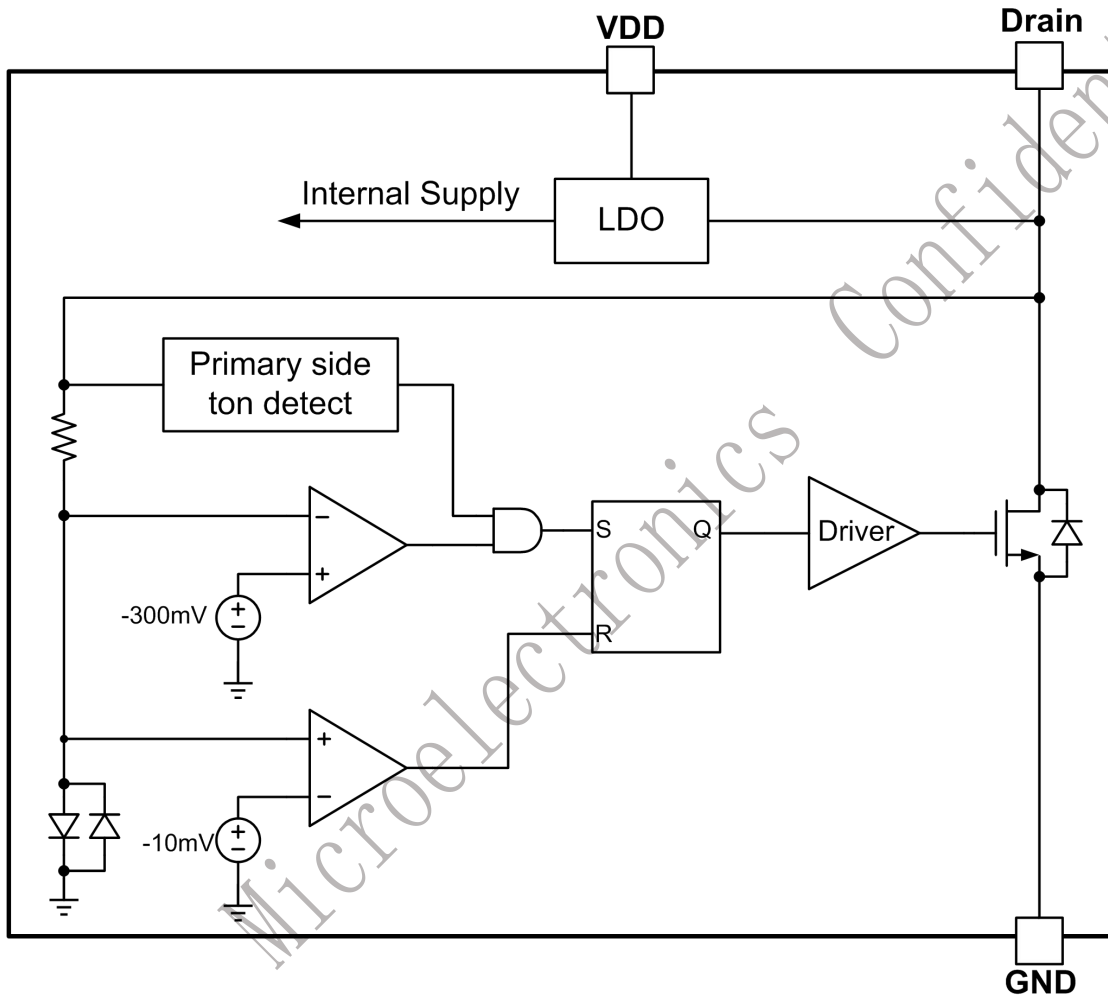
Pin Description

Pin Number	Pin Name	I/O	Description
1,7	NC	---	No Function Pin and Left Floating in Application
2	VDD	P	IC Power Supply Pin and Ceramic Capacitor with Capacitance larger than 0.1uF is Recommended
3,4	GND	P	IC Ground Pin and also the internal Power MOSFET Source Pin
5,6	Drain	I	Internal Power MOSFET Drain Pin

Ordering Information

Part Number	Description
DP3510	SOP-7, Halogen free in T&R, 4000Pcs/Reel

Block Diagram



Absolute Maximum Ratings (Note 1)

Parameter	Value	Unit
Drain Pin Voltage Range	-0.3 to 45	V
VDD DC Supply Voltage	7.4	V
VDD DC Clamp Current	5	mA
Package Thermal Resistance----Junction to Ambient (SOP-8)	165	°C/W
Maximum Junction Temperature	150	°C
Storage Temperature Range	-65 to 150	°C
Lead Temperature (Soldering, 10sec.)	260	°C
ESD Capability, HBM (Human Body Model)	3	kV
ESD Capability, MM (Machine Model)	250	V

Recommended Operation Conditions

Parameter	Value	Unit
Operating Ambient Temperature	-40 to 125	°C

Electrical Characteristics (Ta = 25°C, if not otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
Supply Voltage Section(VDD Pin)						
I _Q	Quiescent Operation Current	VDD=6V,Drain=0V	50	150	200	uA
V _{DD_reg}	HV supply VDD regulation Voltage	Drain=12V	6.7	7.1	7.5	V
I _{HV}	HV supply current	Drain=12V,VDD=5.5V	15		30	mA
V _{DD_ON}	VDD Start-up Voltage	VDD rising	3.7	4	4.3	V
V _{DD_OFF}	VDD Under Voltage Lockout Enter	VDD falling	2.8	3.1	3.4	V
V _{DD_Clamp}	VDD Zener Clamp Voltage	I(V _{DD}) = 5mA		7.4		V
Internal MOSFET and Control Section(Drain Pin)						



Vth_off	Internal synchronous MOSFET turn off threshold voltage		-15	-10	-5	mV
Vth_on	Internal synchronous MOSFET turn on threshold voltage	(Note 2)		-300		mV
Rds_on	Internal synchronous MOSFET on-state resistance			9.2	12	mΩ
Td_on	Internal synchronous MOSFET turn on delay time				200	ns
Td_off	Internal synchronous MOSFET turn off delay time				60	ns
V _{BR}	Internal synchronous MOSFET Drain Source Breakdown Voltage		45			V

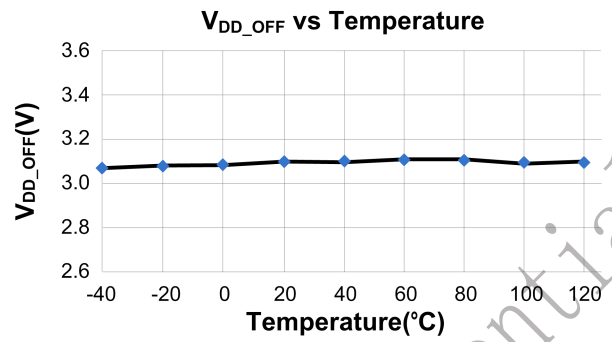
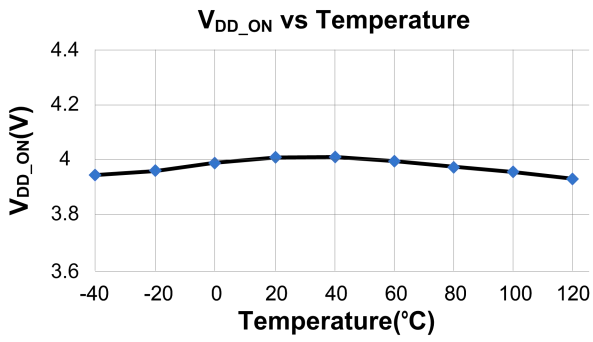
Note 1. Stresses listed as the above "Maximum Ratings" may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to maximum rating conditions for extended periods may remain possibility to affect device reliability.

Note 2. Guaranteed by the Design.

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Characterization Plots



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Operation Description

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- **7.1V Regulator**

In DP3510, the 7.1V regulator charges VDD hold-up capacitor to 7.1V by drawing a current from the Drain pin during the on state of primary side. A capacitor value about 0.1uF is sufficient for both high frequency decoupling and energy storage.

- **System Start-Up Operation**

After system power up, VDD hold up capacitor is charged by the internal LDO through Drain pin.

When VDD pin voltage is below UVLO threshold (3.1V typically), the IC is in sleep mode and the internal synchronous MOSFET is keeping off. The current flows through body diode of the internal synchronous MOSFET. When VDD pin voltage reaches the turn on threshold (4V typically), the IC begins working. The internal synchronous MOSFET can be only turned on during the demagnetization time of the transformer.

- **Turn-on Phase**

When the internal synchronous MOSFET is off, current will flow through its body diode which can generate a negative V_{ds} (<-500mV) across it. The body diode drop voltage V_{ds} is much smaller than

the turn on threshold of DP3510 (-300mV typically), which will turn on the internal synchronous MOSFET after about 200ns turn on delay (T_{d_on}). (Shown in Fig 1)

- **Turn-off Phase**

During the turn-on period of the internal synchronous MOSFET, The DP3510 senses the drop voltage V_{ds} across the on-state resistance of the MOSFET. When V_{ds} is higher than the turn off threshold (-10mV typically), the internal synchronous MOSFET will be turned off after about 60ns turn on delay (T_{d_off}). (Shown in Fig 1)

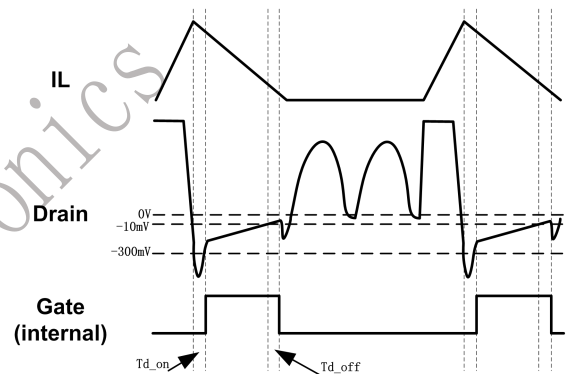


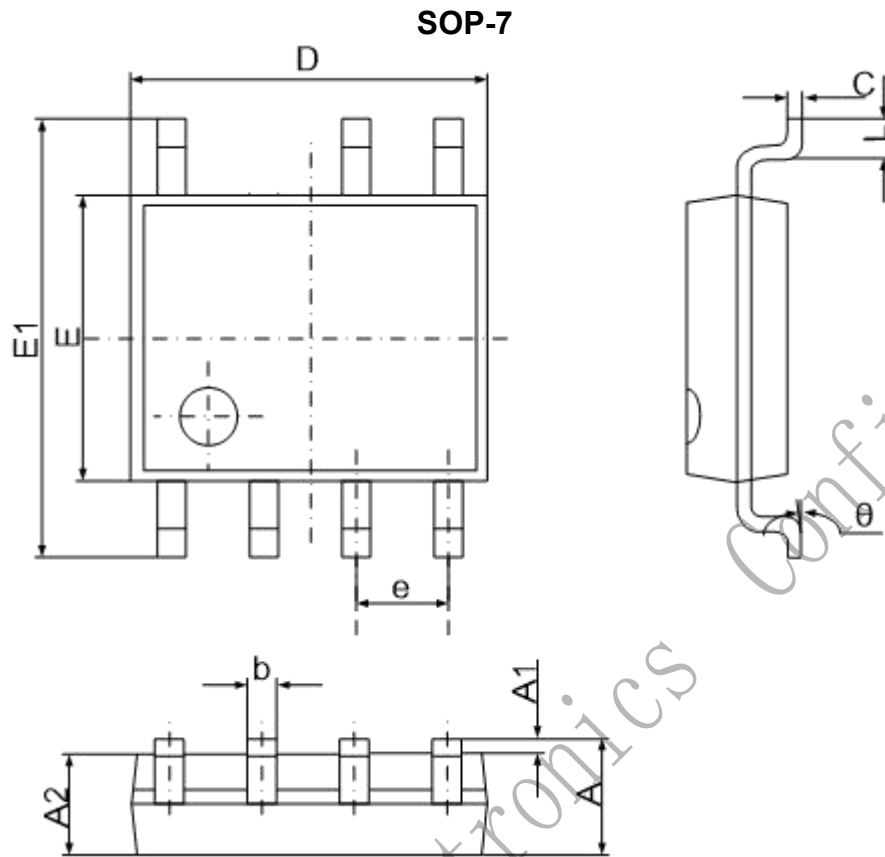
Fig 1

- **Leading Edge Blanking (LEB)**

Each time the internal synchronous MOSFET is switched on, a turn-on spike occurs across the Drain and GND. To avoid premature termination of the switching pulse, an internal leading edge blanking circuit is built in. During this blanking period (1us typically), the turn-off comparator is disabled and cannot switch off the internal synchronous MOSFET.



Package Dimension



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°



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